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THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of:

Jerome DAVIOT et al.

Confirmation No.:

Application No.:

10/688,900

Art Unit:

Filed:

October 21, 2003

Examiner:

For:

AQUEOUS PHOSPHORIC ACID

Attorney Docket No:

060937-0172-US

COMPOSITIONS FOR CLEANING

SEMICONDUCTOR DEVICES

SUBMISSION OF REVOCATION OF ORIGINAL POWER OF ATTORNEY AND GRANT OF NEW POWER OF ATTORNEY

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Enclosed is a copy of the Revocation of Original Power of Attorney and Grant of New Power of Attorney by the Assignee, EKC Technology, Inc. Assignee directs the Patent and Trademark Office to send all future correspondence to:

CUSTOMER NO. 009629 MORGAN, LEWIS & BOCKIUS LLP

1111 Pennsylvania Avenue, N.W. Washington, D.C. 20004

Tel. 202-739-3000

If there is any fee due in connection with the filing of this Submission, please charge the fee to Morgan, Lewis & Bockius LLP Deposit Account No. 50-0310.

Respectfully submitted,

April 26, 2004

By:

Christopher G. Hayden Reg No. 44,750

MORGAN, LEWIS & BÓCKIUS LLP

1111 Pennsylvania Avenue, N.W.

Washington, D.C. 20004

Tel: 202-739-3000 Fax: 202-739-3001



REVOCATION AND POWER OF ATTORNEY

Commissioner for Patents P. O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

EKC Technology, Inc., owner of the entire right, title and interest in, to and under the inventions described and claimed in the patent applications identified in the attached Schedule A, hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, Customer Number 009629, and each of them, its attorneys, to prosecute each of these patent applications, and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to Customer No. 009629, Patent Support Unit, Morgan, Lewis & Bockius LLP, 1111 Pennsylvania Avenue, N.W., Washington, D.C. 20004, and direct all telephone calls to Morgan, Lewis & Bockius LLP at 202-739-3000.

Assignee:

EKC Technology, Inc.

Date: 29 March 2004

Signature:

Typed Name Michael A. Fury

Position/Title Vice President, R&D and Engineering

Address:

2520 Barrington Court, Hayward, California 94545

Schedule A					
App #		Jayenfor(s)	# Filing & Date 1	New Attorney Dockel No	Former Attorney Docket No. 2
	Compositions for Cleaning Organic				
	and Plasma Etched Residues for				
09/903,064	Semiconductor Devices	Small, et al.	07/10/2001	60937-091-US	8317-091-999
	Method of and Apparatus for				
09/874,330	Substrate Pre-Treatment	Maloney, et al.	06/06/2001	60937-111-US	8317-111-999
09/985,870	Chemical Mechanical Polishing Compositions	Small et al	11/06/2001	60027 114 116	9247 444 000
09/905,070	Oxalic Acid as a Semiaqueous	Small, et al.	11/00/2001	60937-114-US	8317-114-999
·	Cleaning Product for Copper and				
10/421,706	Dielectrics	Lee, et al.	04/24/2003	60937-116-US	8317-116-999
10/121,100	Sulfoxide Pyrolid(in)one Alkanolamine			00307-110-00	0017-110-333
10/193,185	Cleaner Composition	Zhou, et al.	07/12/2002	60937-118-US	8317-118-999
	Method for the Deposition of Materials				
09/876,944	from Mesomorphous Films	Vasquez, et al.	06/08/2001	60937-120-US	8317-120-999
	Post Etch Cleaning Composition for				
10/007,134		Payne, et al.	12/04/2001	60937-123-US	8317-123-999
	Photolytic Conversion Process to				
10/263,701		Bravo-Vasquez, et al.	10/04/2002	60937-126-US	8317-126-999
	Cleaning Solutions Including				
	Nucleophilic Amine Compound				
	Having Reduction and Oxidation	1 4 - 1	44/00/0004	00007 407 110	0047 407 000
09/988,545	Potential Method and Compositions for	Lee, et al.	. 11/20/2001	60937-127-US	8317-127-999
	Chemically Treating A Substrate				
10/060,109	Using Foam Technology	Patel, et al.	01/28/2002	60937-129-US	8317-129-999
10,000,100	Cleaning Solution Including	i atci, et ai.	0172072002	00337-123-03	0317-129-999
ļ	Nucleophilic Amine Compound				
j	Having Reduction and Oxidation				
10/135,695	Potential	Lee, et al.	05/01/2002	60937-135-US	8317-135-999
10/448,127	Fluoride Layer and Removing Same	Melvin K. Carter	05/30/2003	60937-137-US	8317-137-999
	Process for the Use of Bis-Choline		·		
	and Tris-Choline in the Cleaning of				İ
	Quartz-Coated Polysilicon and Other				•
10/689,657	Materials	Charm, et al.	10/22/2003	60937-139-US	8317-139-999
	Cleaning Compositions Containing				
	Hydroxylamine Derivatives and	; 1			_ . i
	Process Using Same for Residue	į			
10/689,620	Removal	Zhou, et al.	10/22/2003	60937-140-US	8317-140-999
,	.				. 7
40/000 045	Composition for Exfoliation Agent to				
10/689,616	be Used to Remove Resist Residues	Melvin K. Carter	10/22/2003	60937-141-US	8317-141-999
	Reducing Oxide Loss When Using	!			
	Fluoride Chemistries to Remove Post-	·,	٠.		·
60/467 121	Etch Residues in Semiconductor	les stel	05/02/2002	60027 440 00	9217 142 000
60/467,131	Processing	Lee, et al.	05/02/2003	60937-142-PR	8317-142-888

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	Method for Depositing Patterned				
10/630,301	Films of Materials	Hill, et al.	07/30/2003	60937-143-US	8317-143-999
	Methods for the Deposition of Silver				· .
	and Silver Oxide Films and Patterned				i
10/716,838	Films .	Ruan, et al.	11/18/2003	60937-147-US	8317-147-999
	Semiconductor Process Residue	les shel	00/00/2002	60027 440 110	9247 440 000
10/162,679	Removal Composition and Process	Lee, et al.	06/06/2002	60937-149-US	8317-149-999
	System and Method for Cleaning Workpieces Using Supercritical				
60/460 936	Carbon Dioxide	Fury, et al.	05/13/2003	60937-150-PR	8317-150-888
60/469,826	Carbon bloxide	1 dry, or al.			001, 100 000
	Abrasive-Free Chemical Mechanical	•			
	Polishing Composition and Polishing		·		
10/689,043	Process Containing Same	Yao, et al.	10/21/2003	60937-151-US	8317-151-999
10/689,042	Wet Etch of Titanium-Tungsten Film	Patel, et al.	10/21/2003	60937-152-US	8317-152-999
		•	*		
	Method of Depositing Nanostructured				
10/261,197	Films with Embedded Nanopores	Svendsen, et al.	09/30/2002	60937-153-US	8317-153-999
	Hydrothermal Treatment of		40/22/2002	60027 467 116	9247 467 000
10/280,270	Nanostructured Films	Mukherjee, et al.	10/23/2002	60937-167-US 60937-168-US	8317-167-999 8317-168-999
10/257,469	Inhibition of Titanium Corrosion	Daviot, et al.	10/11/2002	60937-100-03	6317-100-999
40/404 405	— Chemical-Mechanical Polishing — Composition and Process	Small, et al.	03/27/2003	60937-171-US	8317-171-999
10/401,405	Aqueous Phosphoric Acid	Siliali, et al.	03/21/2003	00337-171-03	.0017-171-000
	Compositions for Cleaning				
10/688,900	Semiconductor Devices	Daviot, et al.	.10/21/2003	60937-172-US	8317-172-999
10/000,900	Load Lock System for Supercritical	Daviot, ot at.	10/2 //2000	00001 112 00	
10/465,906	Fluid Cleaning	Fury, et al.	06/18/2003	60937-175-US	8317-175-999
10/100/000	Automated Dense Phase Fluid		·		
10/465,905	Cleaning System	Fury, et al.	06/18/2003	60937-176-US	8317-176-999
	Residue Removers for				
	Electrohydrodynamic Cleaning of		•		
60/455,439	Semiconductors	Robert J. Small	03/18/2003	60937-178-PR	8317-178-888
	Free Radical-Forming Activator				
	Attached to Solid and Used to				
10/361,822	Enhance CMP Formulations	Scott, et al.	02/11/2003	60937-179-US	8317-179-999
	Titanium Carboxylate Films for Use in				
10/377,533	Semiconductor Processing	Hill, et al.	02/26/2003	60937-182-US	8317-182-999
10/422,860	Method of Making Barrier Layers	Maloney, et al.	05/20/2003	60937-183-US	8317-183-999
	Remover Formulation Containing				· . [
60/400 700	Fluoride for Use During	Himanua of at	04/18/2003	60937-185-PR	8317-185-888
60/463,739	Semiconductor Manufacturing Cleaning Composition for Removing	Hirasawa, et al.	04/10/2003	00931-103-FK	0517-100-000
	Resists and Manufacturing Method of	. •.	_		ļ
60/464 125	Semiconductor Devices	Hirasawa, et al.	04/21/2003	60937-186-PR	8317-186-888
60/464,125	Deposition of Permanent Polymer	r masawa, et ai.		10000	
10/422,212 ·	Structures for OLED Fabrication	Roman, et al.	04/23/2003	60937-187-US	8317-187-999
101766,616	Cadolales for SEED 1 abrication	r contain, or an			

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NOTE OF SECURITY OF		VCEPV MARKAS	Fling	New Attorney	Former Attorney
App,#	Tille in the second	Anventor(s)	. Dale	Docket No.	
	Seimconductor Process Residue	VI. WARRANTE VI. AUTO III IV.			
10/442,858	Removal Composition and Process	Wai Mun Lee	05/20/2003	60937-189-US	8317-189-999
10/442,000	Cleaning Compositions and Method of				
10/630,300	Use Thereof	Wai Mun Lee	07/30/2003	60937-194-US	8317-194-999
10/000/000	Compositions and Methods for				
	Rapidly Removing Overfilled				
60/518,337	Substrates	Chelle, et al.	11/10/2003	60937-200-PR	8317-200-888
	CMP Method for Copper, Tungsten,				
	Titanium, Polysilicon, and Other				
	Substrates Using Organosulfonic		40/00/0000	00007 000 110	9247 202 000
10/690,623	Acids as Oxidizers	Carter, et al.	10/23/2003	60937-202-US	8317-202-999
	PeriodicAcid Compositions for	٠.			
	Polishing Nobel Metal/High K	Data de L. Casall	08/14/2003	60937-203-PR	8317-203-888
60/494,954	Substrates	Robert J. Small	06/14/2003	00937-203-PK	0317-203-000
	Cerium Oxide Abrasives for Chemical	Robert J. Small	10/10/2003	60937-204-PR	8317-204-888
60/509,920	Mechanical Polishing	Robert J. Siliali	10/10/2003	00307-204-111	0511 201 000
	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing				
60/E46 726	Salicyclic Acid as a Corrosion Inhibitor	Carter, et al.	11/04/2003	60937-206-PR	8317-206-888
00/310,730	Periodic Acid Compositions for	Our to 17 Ov Cit			
60/494,955	Polishing Ruthenium Substrates	Robert J. Small	08/14/2003	60937-207-PR	8317-207-888
	Chemical-Mechanical Polishing				
10/683,730	Compositions and Process	Small, et al.	10/10/2003	60937-211-US	8317-211-999
10,000,100	Alumia Abrasive for Chemical				
60/514,020	Mechanical Polishing	Philippe H. Chelle	10/27/1999	60937-213-PR	8317-213-888
•		١ .	·		•
	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing		1		
60/502,951	Salicyclic Acid as a Corrosion Inhibitor	Tamilmani, et al.	09/16/2003	60937-214-PR	8317-214-888
	Compositions for Chemical				•
	Mechanical Planarization of Tantalum	0 11 11 11	00/00/0003	60937-215-US	8317-215-999
10/665,417	and Tantalum Nitride	Small, et al.	09/22/2003	60937-213-03	0317-213-333
	Alumina Abrasive for Chemical	Challe et al	12/02/2003	60937-216-PR	8317-216-888
60/526,107	Mechanical Polishing Particulate or Particle-Bound	Chelle, et al.	12/02/2003	00301-210111	
00/500 000	Chelating Agents	Small, et al.	10/10/2003	60937-217-PR	8317-217-888
60/509,922	Particulate or Particle-Bound	Ornan, or an			
10/690,626	Chelating Agents	Small, et al.	10/23/2003	60937-217-US	·8317-217-999
10/030,020	Chemical Mechanical Polishing of STI				
	Features on Semiconductors: Water			·	-
60/533,054	Polishing with Ceria Slurries	Yu, et al	12/30/2003	60937-223-PR	8317-223-888
				•	
	Removal of Post Etch Residues and		·		
	Copper Contamination From Low-K				
	Dielectrics Using Superciritcal CO2				
60/511,949	with Diketone Additives	Jerome Daviot	10/14/2003	60937-225-PR	8317-225-888
	Tatalanda Annanakan fan Cub girata	1	j ·	I	•
	Method and Apparatus for Substrate Pre-Treatment	Lee, et al.	10/29/2003	60937-226-US	, 8317-226-999 ·

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	Method of Chemically Mechanically				
60/515,450	Polishing Substrates	Brandon S. Scott	10/30/2003	60937-228-PR	8317-228-888